



High-end Power Semiconductor Manufacturer

# ZP800A 1000-2000V Standard Rectifier Diode

- High power cycling capability
- Low on-state and switching losses
- Optimized for line frequency rectifiers
- Designed for traction and industrial applications



Average forward current				I <sub>FAV</sub>		800 A					
Repetitive peak reverse voltage				V <sub>RRM</sub>		1000 – 2000 V					
V <sub>RRM</sub> , V	1000	1100	1200	1300	1400	1500	1600	1800	2000		
Voltage code	10	11	12	13	14	15	16	18	20		
T <sub>j</sub> , °C				-60 – 190							

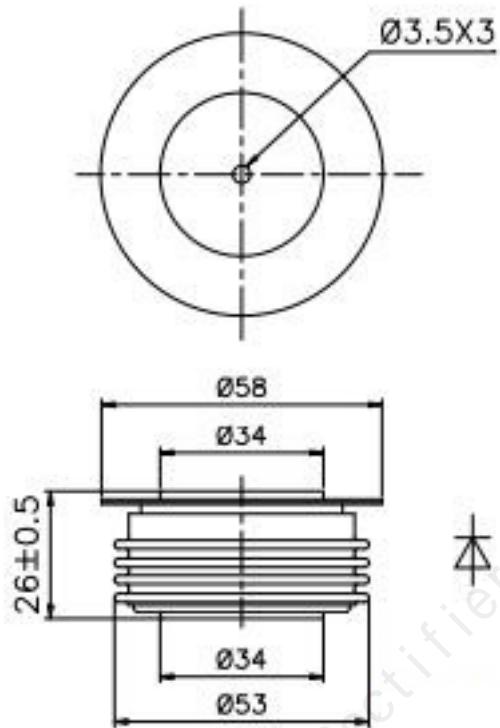
## MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values		Test conditions	
<b>ON-STATE</b>						
I <sub>FAV</sub>	Average forward current	A	800		T <sub>c</sub> =100 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I <sub>FRMS</sub>	RMS forward current	A	1256		T <sub>c</sub> =145 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I <sub>FSM</sub>	Surge forward current	kA	12.0	T <sub>j</sub> =T <sub>j</sub> max	180° half-sine wave; 50 Hz (t <sub>p</sub> =10 ms); single pulse; V <sub>R</sub> =0 V;	
			13.0	T <sub>j</sub> =25 °C	180° half-sine wave; 60 Hz (t <sub>p</sub> =8.3 ms); single pulse; V <sub>R</sub> =0 V;	
I <sup>2</sup> t	Safety factor	A <sup>2</sup> s·10 <sup>3</sup>	720	T <sub>j</sub> =T <sub>j</sub> max	180° half-sine wave; 50 Hz (t <sub>p</sub> =10 ms); single pulse; V <sub>R</sub> =0 V;	
			950	T <sub>j</sub> =25 °C	180° half-sine wave; 60 Hz (t <sub>p</sub> =8.3 ms); single pulse; V <sub>R</sub> =0 V;	
<b>BLOCKING</b>						
V <sub>RRM</sub>	Repetitive peak reverse voltages	V	1000–2000	T <sub>j min</sub> < T <sub>j</sub> <T <sub>j max</sub> ;	180° half-sine wave; 50 Hz;	
V <sub>RSM</sub>	Non-repetitive peak reverse voltages	V	1100–2100	T <sub>j min</sub> < T <sub>j</sub> <T <sub>j max</sub> ;	180° half-sine wave; 50 Hz;single pulse;	
V <sub>R</sub>	Reverse continuous voltages	V	0.75·V <sub>RRM</sub>	T <sub>j</sub> =T <sub>j</sub> max;		
<b>THERMAL</b>						
T <sub>stg</sub>	Storage temperature	°C	-60–50			
T <sub>j</sub>	Operating junction temperature	°C	-60–190			
<b>MECHANICAL</b>						
F	Mounting force	kN	9.0–11.0			
a	Acceleration	m/s <sup>2</sup>	50 100	Device unclamped Device clamped		

## CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
<b>ON-STATE</b>					
V <sub>FM</sub>	Peak forward voltage, max	V	1.61	T <sub>j</sub> =25 °C; I <sub>FM</sub> =2512 A	
V <sub>F(TO)</sub>	Forward threshold voltage, max	V	1.01	T <sub>j</sub> =T <sub>j max</sub> ; 0.5 π I <sub>FAV</sub> < I <sub>T</sub> < 1.5 π I <sub>FAV</sub>	
r <sub>T</sub>	Forward slope resistance, max	mΩ	0300		
<b>BLOCKING</b>					
I <sub>RRM</sub>	Repetitive peak reverse current, max	mA	50	T <sub>j</sub> =T <sub>j max</sub> ; V <sub>R</sub> =V <sub>RRM</sub>	
<b>THERMAL</b>					
R <sub>thjc</sub>	Thermal resistance, junction to case, max	°C/W	0.036	Direct current	Double side cooled
R <sub>thjc-A</sub>			0.079		Anode side cooled
R <sub>thjc-K</sub>			0.065		Cathode side cooled
R <sub>thck</sub>	Thermal resistance, case to heatsink, max	°C/W	0.008	Direct current	
<b>MECHANICAL</b>					
w	Weight, typ	g	180		
D <sub>s</sub>	Surface creepage distance	mm (inch)	23.69 (0.933)		
D <sub>a</sub>	Air strike distance	mm (inch)	19.10 (0.752)		

## OVERALL DIMENSIONS



ZT40

All dimensions in millimeters